

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1 1. (Currently amended) A semiconductor device, comprising:
2 a semiconductor base comprising a plurality of first semiconductor regions having
3 a first conductivity type, a plurality of second semiconductor regions having a second
4 conductivity type formed in a specific surface portion of said first semiconductor regions, and a
5 plurality of third semiconductor regions having the first conductivity type formed in a specific
6 surface portion of said second semiconductor regions; and
7 a first electrode formed directly above said second semiconductor region that is
8 between said first semiconductor region and said third semiconductor regions,
9 wherein~~[[.]]~~ a first region, ~~in which one of said comprising a first plurality of~~ third
10 semiconductor regions exhibiting a first surface area~~[[.]]~~ is formed at a center of said
11 semiconductor base, ~~[[and]]~~
12 ~~wherein~~ a second region, ~~in which another of said comprising a second plurality~~
13 ~~of~~ third semiconductor regions exhibits a second surface area larger than said first surface area, ~~is~~
14 ~~formed at a circumference of said semiconductor base so as to enclose~~ completely surrounds
15 said first region,
16 wherein said first plurality of third semiconductor regions and said second
17 plurality of third semiconductor regions, each comprise a first device stacked on top of a second
18 device.

1 2. (Currently amended) The semiconductor device according to claim 1,
2 wherein said first and second plurality of [[said]] third semiconductor regions are formed to be
3 spaced from each other.

1 3. (Currently amended) The semiconductor device according to claim 1,
2 wherein said plurality of second ~~plurality of~~ semiconductor regions are formed in a belt shape.

1 4. (Currently amended) The semiconductor device according to claim 3,
2 wherein said plurality of second semiconductor regions are formed side by side with a space
3 therebetween.

1 5-6. (Canceled)

1 7. (Withdrawn) A semiconductor device, comprising a semiconductor base
2 including a first semiconductor region having a first conductivity type, a second semiconductor
3 region having a second conductivity type formed in a surface region of said first semiconductor
4 region, and a third semiconductor region having the first conductivity type formed in a surface
5 region of said second semiconductor region,
6 wherein said third semiconductor region is formed along a first direction such that
7 a rate at which it occupies said second semiconductor region is larger at a peripheral part of said
8 semiconductor base than at a center part thereof, and formed along a second direction
9 perpendicular to said first direction such that a rate at which said third semiconductor region
10 occupies said second semiconductor region is larger at said peripheral part of said semiconductor
11 base than at said center part thereof.

1 8. (Withdrawn) The semiconductor device according to claim 7, wherein
2 said second semiconductor region is formed in a belt shape, and said first direction is defined in
3 parallel with an extending direction of said second semiconductor region.

1 9. (Withdrawn) The semiconductor device according to claim 7, wherein
2 said second semiconductor region is formed in an island shape, and said first direction is defined
3 in parallel with or perpendicularly to a part of edges of said semiconductor device.

10. (Withdrawn) A semiconductor device, comprising:

a semiconductor base comprising a first semiconductor region having a first conductivity type, a second semiconductor region having a second conductivity type formed in a surface region of said first semiconductor region, and a third semiconductor region having the first conductivity type formed in a surface region of said second semiconductor region;
an insulating film formed on said second semiconductor region sandwiched between said first semiconductor region and said third semiconductor region; and
a first electrode formed on said insulating film,
wherein said insulating film comprises a first region formed at a center region of said semiconductor base to have a first thickness, and a second region formed to have a second thickness thinner than said first region at a circumference of said semiconductor base so as to enclose said first region.

11. (Withdrawn) A semiconductor device, comprising:

a semiconductor base comprising a first semiconductor region having a first conductivity type, a second semiconductor region having a second conductivity type formed in a surface region of said first semiconductor region, and a third semiconductor region having the first conductivity type formed in a surface region of said second semiconductor region;
an insulating film formed on said second semiconductor region sandwiched between said first semiconductor region and said third semiconductor region; and
a first electrode formed on said insulating film,
wherein said second semiconductor region comprises a first region formed at a center of said semiconductor base to have a first impurity concentration, and a second region formed to have a second impurity concentration lower than said first impurity concentration at a circumference of said semiconductor base so as to enclose said first region.